## **Analog Power**

## N-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8PP saves board space
- Fast switching speed
- High performance trench technology

	PRODUCT SUMMARY					
	V <sub>DS</sub> (V)	r <sub>DS</sub>	$(on)$ m( $\Omega$ )	I <sub>D</sub> (A)		
	100	56 @	56 @ $V_{GS} = 10V$			
	100	88 @ $V_{GS} = 5.5V$		6.2		
1		SOIC- Top \	-	D		
	s 🗆	1	8 🖽 D	Ļ		
<b>W</b> .	S 🗆	2	7 🗖 D	G⊶⊣⊟		

6 🖽 D

5 🖽 D

S 🖂 3

G 🖂 4

S N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Maximum	Units				
Drain-Source Voltage			100	V			
Gate-Source Voltage	V <sub>GS</sub>	20	v				
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	Τ_	7.8				
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	6.3	А			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	50					
Continuous Source Current (Diode Conduction) <sup>a</sup>	Is	2.3	А				
	T <sub>A</sub> =25°C	PD	5.0	W			
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	гD	3.2	vv			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
	t <= 10 sec	П	25	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	R <sub>0JA</sub>	65	°C/W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

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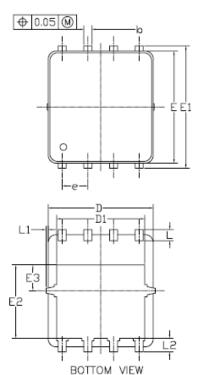
Devenuetor	C1 - 1	To at Com liting a	Limits			TT *4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = 12 V$			100	nA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 80 V, V_{GS} = 0 V$			1	uA	
Zero Gate voltage Drain Current	IDSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$	$_{\rm s} = 0 \text{ V}, \text{ T}_{\rm J} = 55^{\circ}\text{C}$	5			
On-State Drain Current <sup>A</sup>	ID(on)	$V_{DS} = 5 V, V_{GS} = 10 V$	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$			56		
Drain-Source On-Resistance <sup>A</sup>	fDS(on)	$V_{GS} = 5.5 \text{ V}, I_D = 1 \text{ A}$			88	mΩ	
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 1 \text{ A}$		40		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_S = 1 A, V_{GS} = 0 V$		0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	X- 15 X/ X/ 45 X/		10			
Gate-Source Charge	Qgs	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 1 \text{ A}$		5		nC	
Gate-Drain Charge	Qgd	ID = I A		10			
Turn-On Delay Time	td(on)			9			
Rise Time	tr	$V_{DD}$ = 15 V, $R_L$ = 6 $\Omega$ , ID = 1 A,		10		nS	
Turn-Off Delay Time	td(off)	VGEN = 10 V		40			
Fall-Time	tf			10			

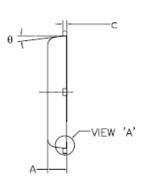
Notes

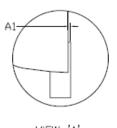
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information







<u>VIEW 'A'</u> (SCALE 5:1)

and the oto	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES				
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.85	0.95	1.00	0.033	0.037	0.039		
A1	0.00		0.05	0.000		0.002		
b	0.30	0.40	0.50	0.012	0.016	0.020		
с	0.15	0.20	0.25	0.006	0.008	0.010		
D	5.20 BSC				0.205 BSC			
D1	4.35 BSC				0.171 BSC			
Е	5.55 BSC				0.219 BSC			
E1	6.05 BSC				0.238 BSC			
E2	3.625 BSC				0.143 BSC			
E3	1.275 BSC				0.050 BSC			
e	1.27 BSC				0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026		
L1	0		0.15	0		0.006		
L2	0.68 REF				0.027 REF			
θ	0°		10°	0°		10°		